



### 30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

-70 A

#### **Features**

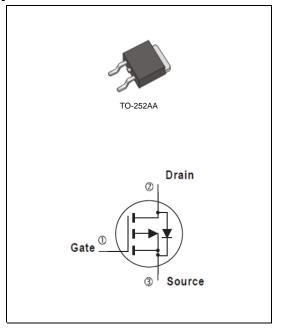
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@-10V,I<sub>D</sub>@-10A<8.5mΩ
- $R_{DS(ON)}$ ,  $V_{GS}$ @-4.5V, $I_D$ @-8A<14 $m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS2.0 (2011/65/EU & 2015/865/EU directive)
- Green molding compound as per IEC61249 Std.. (Halogen Free)

### **Mechanical Data**

• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams



# **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAME	ΓER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage		$V_{DS}$	-30	V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V
Oscilla de Baris Oscila	T <sub>C</sub> =25°C	l <sub>D</sub>	-70	
Continuous Drain Current	T <sub>C</sub> =100°C		-44	А
Pulsed Drain Current <sup>(Note 1)</sup>	T <sub>C</sub> =25°C	I <sub>DM</sub>	-280	
Power Dissipation	T <sub>C</sub> =25°C	Po	63	10/
	T <sub>C</sub> =100°C		25	W
Continuous Drain Current	T <sub>A</sub> =25°C	I <sub>D</sub>	-11	А
	T <sub>A</sub> =70°C		-8.8	А
Power Dissipation	T <sub>A</sub> =25°C	_	2.0	10/
Power Dissipation	T <sub>A</sub> =70°C	Po	1.3	W
Operating Junction and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55~150	°C
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	$R_{ heta JC}$	2.0	90.447
	Junction to Ambient	$R_{\theta JA}$	62.5	°C/W

• Limited only By Maximum Junction Temperature





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =-250uA	-30	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250uA$	-1.0	-1.5	-2.5	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V,I <sub>D</sub> =-10A	-	7.1	8.5	mΩ	
Dialii-Source Off-State Resistance		V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-8A	-	10	14		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V	-	-	-1.0	uA	
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 6)							
Total Gate Charge	$Q_g$	V <sub>DS</sub> =-15V, I <sub>D</sub> =-10A, V <sub>GS</sub> =-4.5V <sup>(Note 1,2)</sup>	-	27	-	nC	
Gate-Source Charge	$Q_gs$		-	8.4	-		
Gate-Drain Charge	$Q_gd$	V <sub>GS</sub> =-4.5 V	-	8.7	-		
Input Capacitance	Ciss	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	3228	-	pF	
Output Capacitance	Coss		-	396	-		
Reverse Transfer Capacitance	Crss	I=1.0IVII IZ	-	254	-		
Turn-On Delay Time	td <sub>(on)</sub>	\\\\ 45\\\\D\\\AA	-	10	-		
Turn-On Rise Time	t <sub>r</sub>	$V_{DS}$ =-15V,ID=-1A, $V_{GS}$ =-10V, $R_{G}$ =6 $\Omega$	-	13	-	ns	
Turn-Off Delay Time	td <sub>(off)</sub>	(Note 1,2)	-	111	-		
Turn-Off Fall Time	t <sub>f</sub>		-	51	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	ı		_	-	-70	А	
Diode Forward Current	I <sub>S</sub>		_				
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =-1A,V <sub>GS</sub> =0V	-	-0.7	-1.0	V	

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial  $T_J$  =25°C.
- 4. The maximum current rating is package limited
- 5. Roja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper
- 6. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

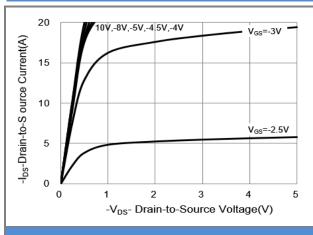
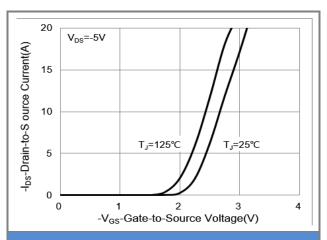


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

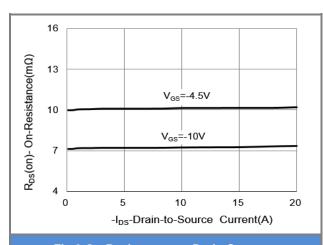


Fig.3 On-Resistance vs. Drain Current

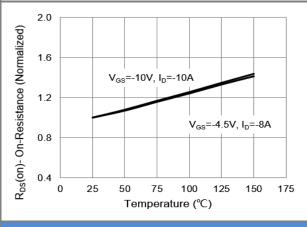


Fig.4 On-Resistance vs. Junction temperature

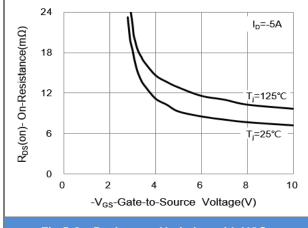
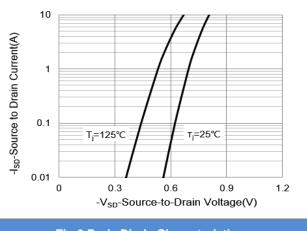


Fig.5 On-Resistance Variation with VGS.



**Fig.6 Body Diode Characteristics** 





### **TYPICAL CHARACTERISTIC CURVES**

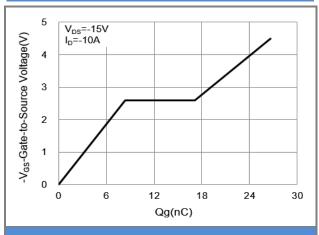


Fig.7 Gate-Charge Characteristics

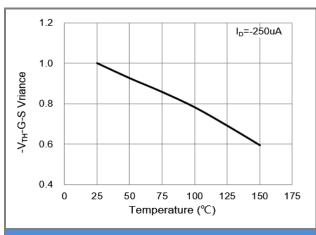
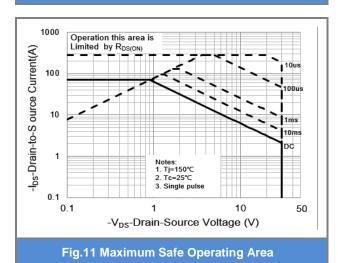


Fig.9 Threshold Voltage Variation with Temperature.



1.2 I<sub>D</sub>=-250uA BVDSS- Drain-to-Source Voltage(V) 1.1 1.0 0.9 8.0 0 25 125 150 175 50 75 100 Temperature (°C)

Fig.8 Breakdown Voltage Variation vs. Temperature

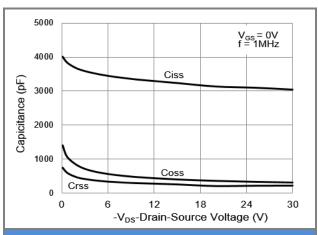
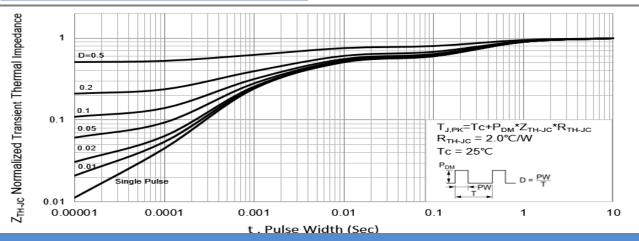


Fig.10 Capacitance vs. Drain-Source Voltage.





### **TYPICAL CHARACTERISTIC CURVES**

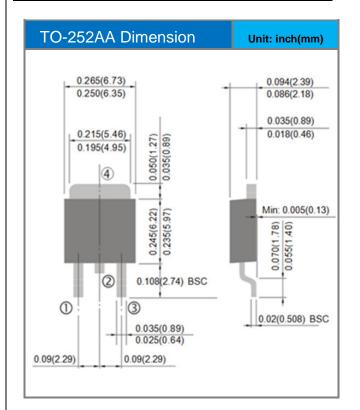


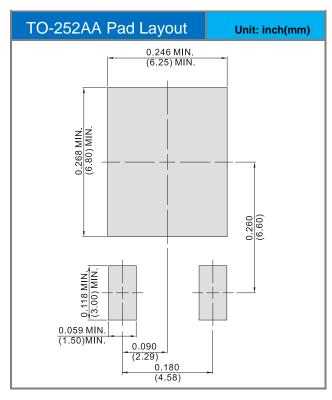
**Fig.12 Normalized Thermal Transient Impedance** 





### **Packaging Information**









### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJD70P03_L2_00001	TO-252AA	3,000pcs / 13" reel	D70P03	Halogen free	





#### Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are
  responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no
  representation or warranty that such applications will be suitable for the specified use without further testing or
  modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

## Panjit:

PJD70P03\_L2\_00001